



MG120R080A

主要参数 MAIN CHARACTERISTICS

I_D	30A
V_{CE}	1200V
$R_{dson-typ}$ (@ $V_{gs}=18V$)	50m Ω
Q_g-typ	90nC

用途

- 光伏逆变器
- 开关模式电源
- 高压 DC/DC 转换器
- 电池充电器
- 电动驱动
- 脉冲电源应用

APPLICATIONS

- Solar Inverters
- Switch Mode Power Supplies
- High Voltage DC/DC Converters
- Battery Chargers
- Motor Drives
- Pulsed Power applications

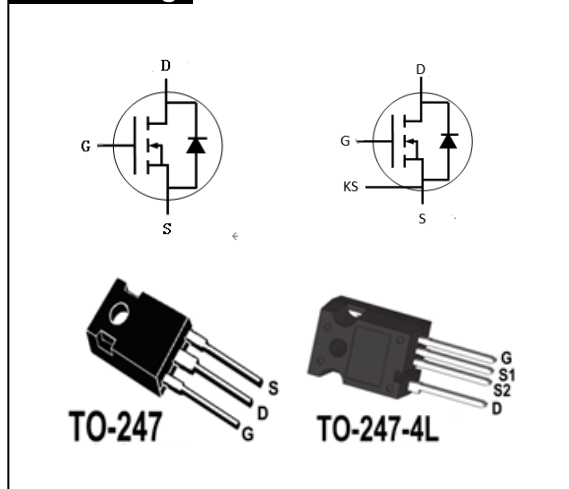
产品特性

- 高阻断电压
- 低导通电阻
- 低电容高速开关
- 易于驱动
- 雪崩强度高
- RoHS 产品

FEATURES

- High Blocking Voltage
- Low On-Resistance
- High Speed Switching with Low Capacitances
- Easy to Parallel and Simple to Drive
- Avalanche Ruggedness
- RoHS product

封装 Package



订货信息 ORDER MESSAGE

订货型号 Order codes	印记 Marking	封装 Package
无卤-条管 Halogen-Free-Tube		
MG120R080A-GE-BR	MG120R080A	TO-247
MG120R080A-GH-BR	MG120R080A	TO-247-4L





绝对最大额定值 ABSOLUTE RATINGS (Tc=25°C)

项 目 Parameter	符 号 Symbol	数 值 Value	单 位 Unit	测试条件 Tests conditions
最高漏极-源极直流电压 Drain-Source Voltage	V _{DSmax}	1200	V	V _{GS} =0V, I _D =100μA
最高栅源电压 Gate-Source Voltage	V _{GSmax}	-8/+22	V	Absolute maximum values
工作栅源电压 Gate-Source Voltage	V _{GSop}	-5/+18	V	Recommended operational values
连续漏极电流 Drain Current -continuous	I _D	30	A	V _{GS} =18V, T _C =25°C
		20	A	V _{GS} =18V, T _C =100°C
最大脉冲漏极电流 Drain Current - pulse	I _{DM}	80	A	Pulse width limited by T _{jmax}
耗散功率 Power Dissipation	P _D	300	W	T _C =25°C, T _J =175°C
最高结温及存储温度 Operating and Storage Temperature Range	T _J , T _{STG}	-55~+175	°C	
引线最高焊接温度 Maximum Lead Temperature for Soldering Purposes	T _L	300	°C	





电特性 ELECTRICAL CHARACTERISTICS

项 目 Parameter	符 号 Symbol	测试条件 Tests conditions	最小 Min	典型 Typ	最大 Max	单位 Units
漏-源击穿电压 Drain-Source Voltage	BV_{DSS}	$I_D=100\mu A, V_{GS}=0V$	1200	-	-	V
阈值电压 Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D=5mA, T_C=25^\circ C$	2.0	3.2	4.5	V
		$V_{DS} = V_{GS}, I_D=5mA, T_C=175^\circ C$		2		
零栅压下漏极漏电流 Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=1200V, V_{GS}=0V, T_C=25^\circ C$	-	1	100	μA
栅极体漏电流 Gate-body leakage current	I_{GSS}	$V_{DS}=0V, V_{GS} =18V$	-	10	200	nA
导通电阻 Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS} =18V, I_D=20A, T_C=25^\circ C$	-	50	80	m Ω
		$V_{GS} =18V, I_D=20A, T_C=175^\circ C$		80		m Ω
跨导 Transconductance	g_{fs}	$V_{DS} =18V, I_D=20A, T_J = 25^\circ C$	-	17.5	-	S
		$V_{DS} = 18V, I_D=20A, T_J =175^\circ C$		16.5		S
输入电容 Input capacitance	C_{iss}	$V_{DS}=1000V,$ $V_{GS} =0V,$ $f=1.0MHz,$ $V_{AC}=25mV$	-	1680	-	pF
输出电容 Output capacitance	C_{oss}		-	70	-	pF
反向传输电容 Reverse transfer capacitance	C_{rss}		-	8	-	pF
导通开关能量 Turn-On Switching Energy	E_{ON}	$V_{DS}=800V, V_{GS}=-5/18V, I_D=20A,$ $R_{G(ext)} =0\Omega, L=160\mu H$	-	450	-	μJ
关断开关能量 Turn-Off Switching Energy	E_{OFF}		-	110	-	
延迟时间 Turn-On delay time	$t_{d(on)}$	$V_{DD}=800V, V_{GS}=-5/18V$ $I_D =20A, R_{G(ext)} =0\Omega,$ Timing relative to VDS	-	28	-	ns
上升时间 Turn-On rise time	t_r		-	65	-	ns
延迟时间 Turn-Off delay time	$t_{d(off)}$		-	24	-	ns
下降时间 Turn-Off Fall time	t_f		-	20	-	ns
栅电阻 Intrinsic gate resistance	R_G	$f = 1 MHz, V_{AC}=25mV$	-	6.0	-	Ω
栅-源电荷 Gate-Source charge	Q_{gs}	$V_{DD}=800V, V_{GS}=-5/18V, I_D =20A$		32		nC
栅-漏电荷 Gate-Drain charge	Q_{gd}			23		
栅极电荷总量 Total Gate Charge	Q_g			90		



漏-源二极管特性 Drain-Source Diode Characteristics

项 目 Parameter	符 号 Symbol	测试条件 Tests conditions	典型 Typ	最大 Max	单位 Units
正向压降 Drain-Source Diode Forward Voltage	V_{SD}	$V_{GS} = -5V, I_{SD} = 10A, T_J = 25^\circ C$	3.5		V
		$V_{GS} = -5V, I_{SD} = 10A, T_J = 175^\circ C$	3.2		V
正向最大连续电流 Maximum Continuous Drain -Source Diode Forward Current	I_S	$T_C = 25^\circ C$	-	30	A
反向恢复时间 Reverse recovery time	t_{rr}		16		ns
反向恢复电荷 Reverse recovery charge	Q_{rr}	$V_{GS} = -5V, I_{SD} = 20A, V_R = 800V,$ $dif/dt = 1200A/\mu s$	75		nC
峰值反向恢复电流 Peak Reverse Recovery Current	I_{rrm}		6		A

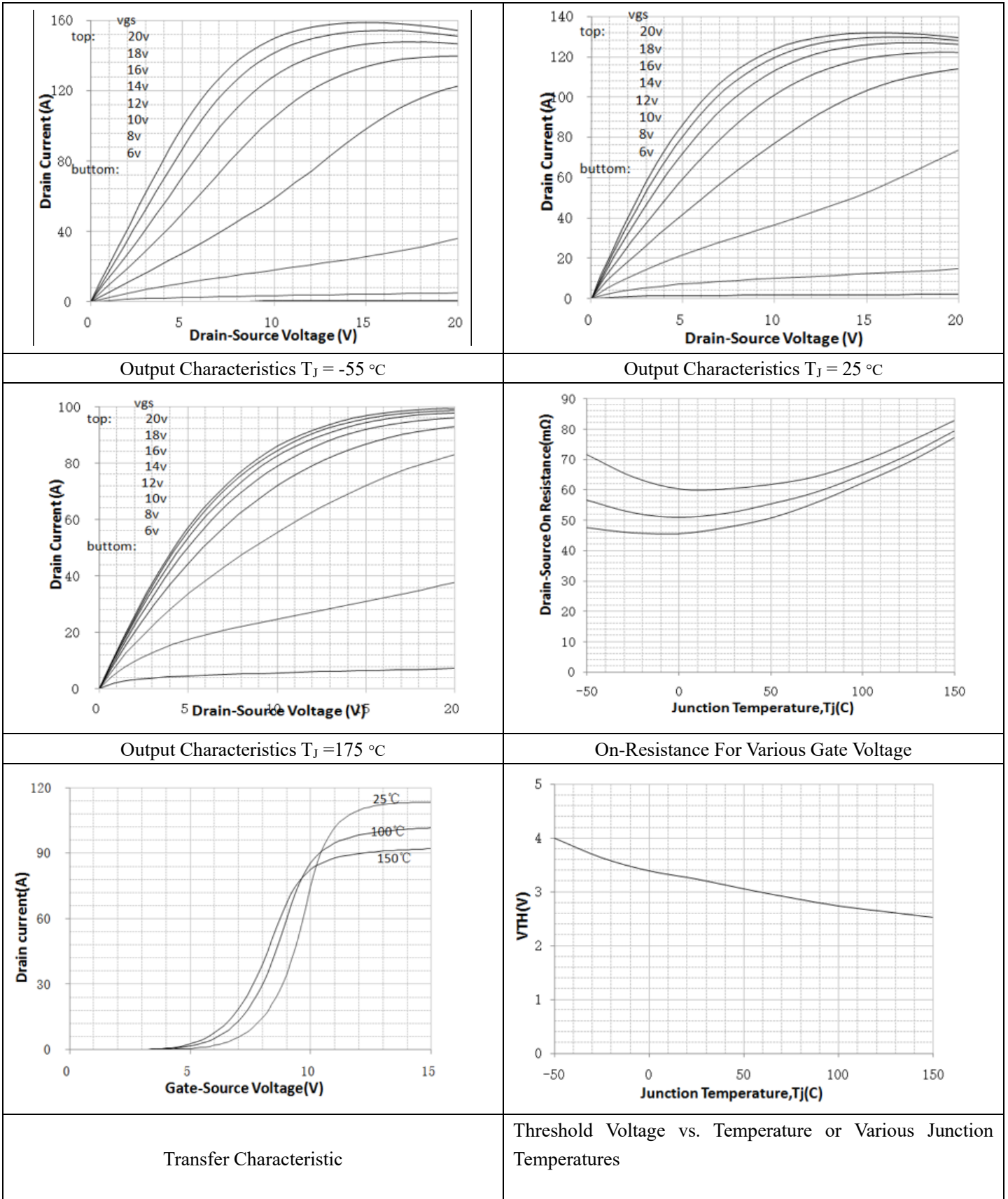
热特性 THERMAL CHARACTERISTIC

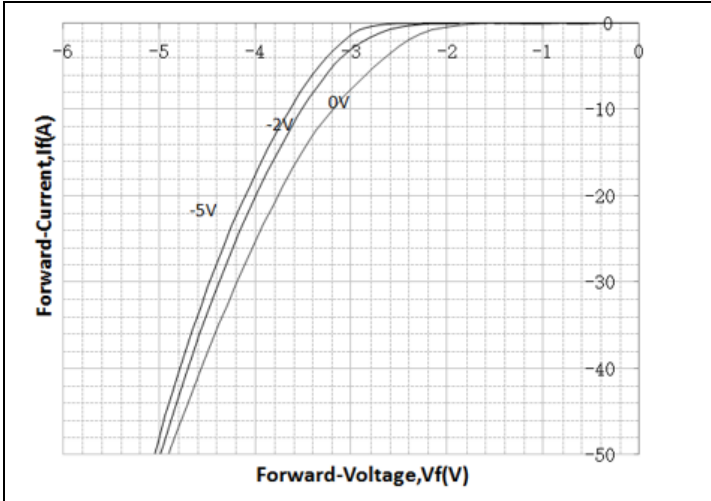
项 目 Parameter	符 号 Symbol	典型 Typ	单位 Unit
结到管壳的热阻 Thermal Resistance, Junction to Case	$R_{th(j-c)}$	0.45	$^\circ C/W$
结到环境的热阻 Thermal Resistance, Junction to Ambient	$R_{th(j-A)}$	35	$^\circ C/W$



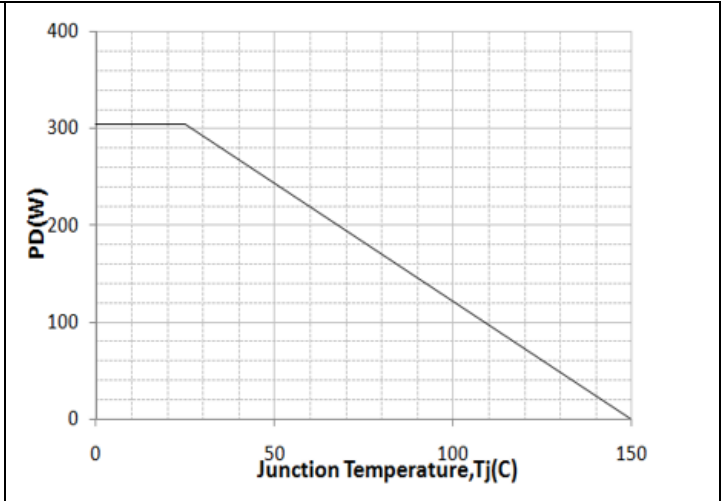


典型性能 Typical Performance

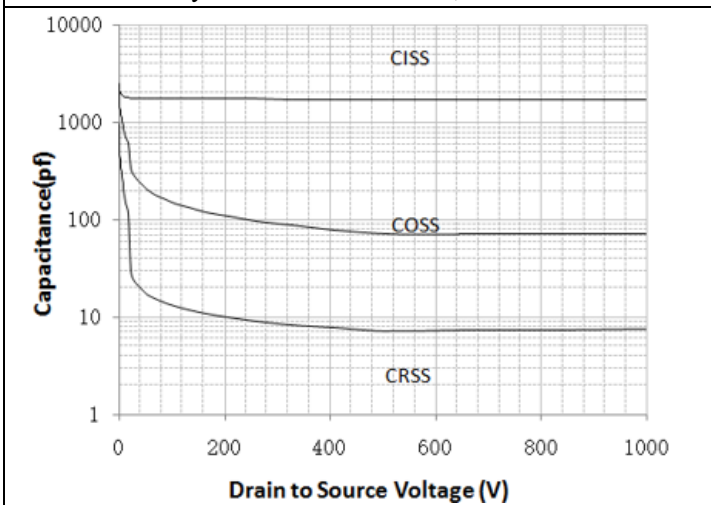




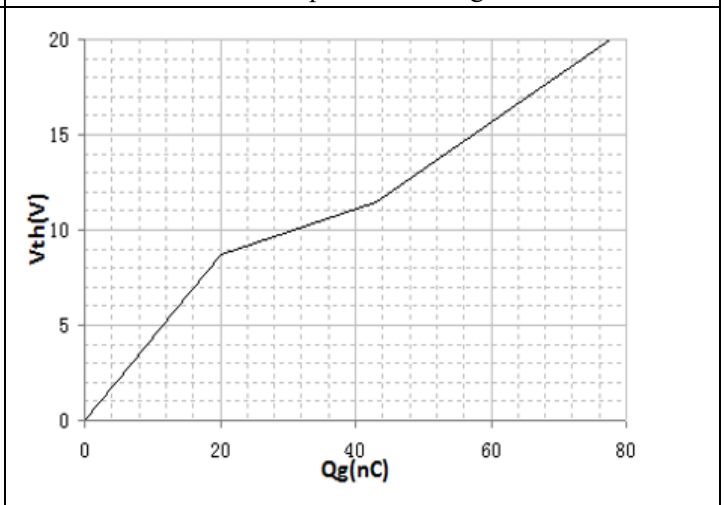
Body Diode Characteristics,



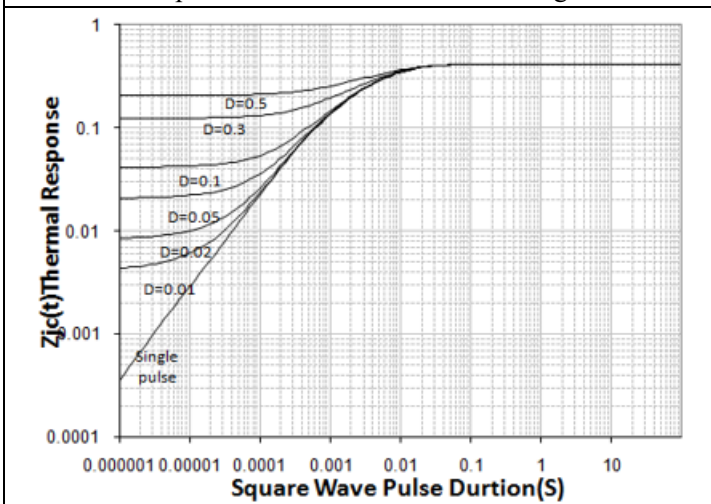
Power Dissipation Derating



Capacitances vs. Drain-Source Voltage



Gate Charge Characteristics



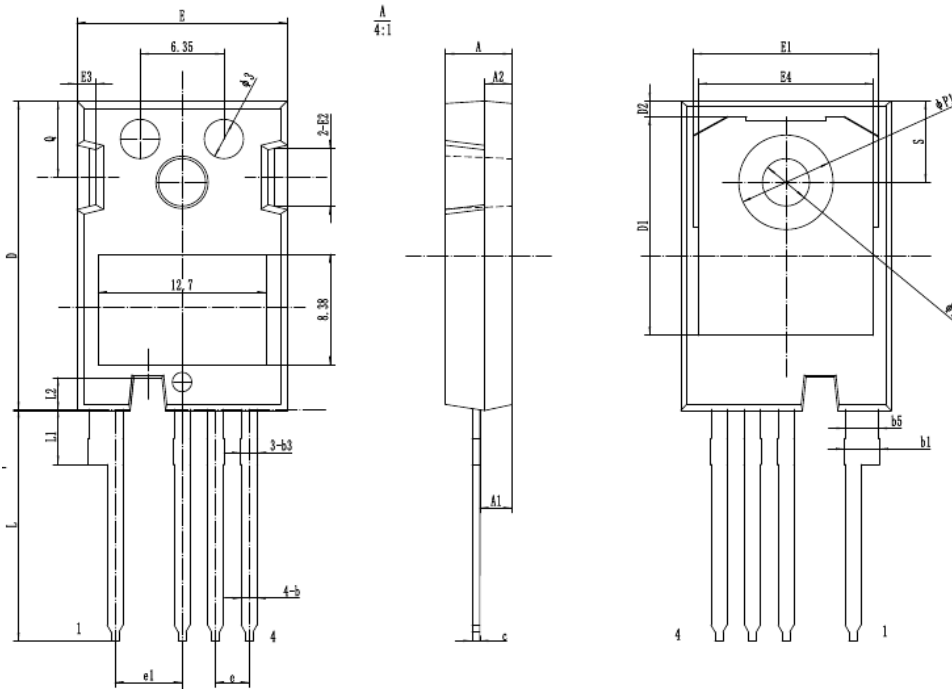
Transient Thermal Impedance



外形尺寸 PACKAGE MECHANICAL DATA

TO-247-4L

单位 Unit: mm

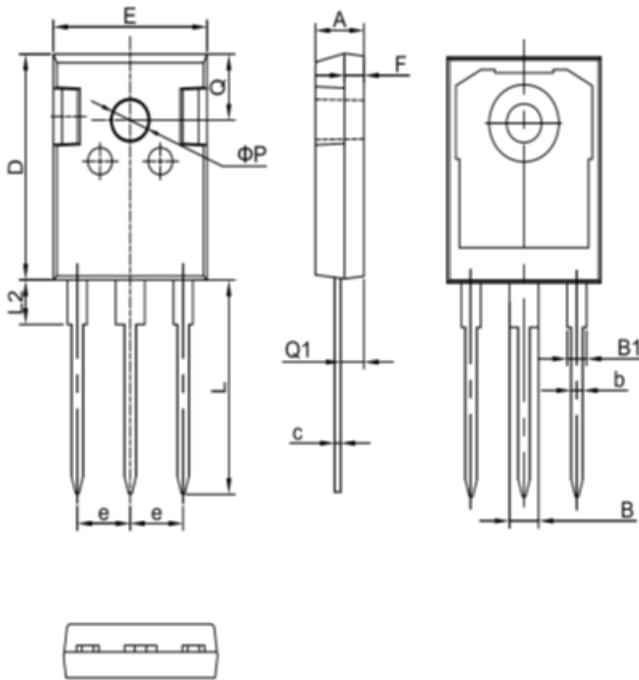


SYMBOL	mm		
	MIN	NOM	MAX
*A	4.83	5.02	5.21
A1	2.29	2.41	2.54
A2	1.91	2.00	2.16
*b	1.07	1.20	1.33
b1	2.39	2.67	2.94
b3	1.07	1.30	1.60
b5	2.39	2.53	2.69
*c	0.55	0.60	0.68
*D	23.30	23.45	23.60
D1	16.25	16.55	17.65
D2	0.95	1.19	1.25
*E	15.75	15.94	16.13
E1	13.10	14.02	14.15
E2	3.68	4.40	5.10
E3	1.00	1.45	1.90
E4	12.38	13.26	13.43
*e	2.54BSC		
e1	5.08BSC		
*L	17.31	17.57	17.82
*L1	3.97	4.19	4.37
*L2	2.30	2.50	2.65
* ϕP	3.51	3.61	3.65
* $\phi P1$	7.19REF		
*Q	5.49	5.79	6.00
S	6.04	6.17	6.30



TO-247

单位 Unit: mm



符号 symbol	MIN	MAX
A	4.90	5.10
B	2.95	3.35
B1	1.95	2.35
b	1.15	1.35
c	0.50	0.70
D	20.90	21.10
E	15.70	15.90
e	5.34	5.54
F	1.90	2.10
L	19.40	20.40
L2	4.03	4.23
Q	6.00	6.40
Q1	2.30	2.50
P	3.50	3.70

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